

<b>SANYO</b>	No.1030E	<b>2SB926/2SD1246</b>
		PNP/NPN Epitaxial Planar Silicon Transistors
<b>Large-Current Driving Applications</b>		

**Applications**

- Power supplies, relay drivers, lamp drivers, electrical equipment

**Features**

- Adoption of FBET, MBIT processes
- Low saturation voltage
- Large current capacity and wide ASO

( ): 2SB926

Absolute Maximum Ratings/ $T_a = 25^\circ\text{C}$ 

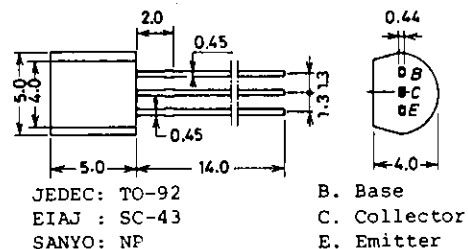
			unit
Collector to base voltage	$V_{CB0}$	(-) $30$	V
Collector to emitter voltage	$V_{CE0}$	(-) $25$	V
Emitter to base voltage	$V_{EBO}$	(-) $6$	V
Collector current	$I_C$	(-) $2$	A
Collector Current(Pulse)	$I_{CP}$	(-) $5$	A
Collector dissipation	$P_C$	$0.75$	W
Junction temperature	$T_j$	$150$	$^\circ\text{C}$
Storage temperature	$T_{stg}$	$-55 \sim +150$	$^\circ\text{C}$

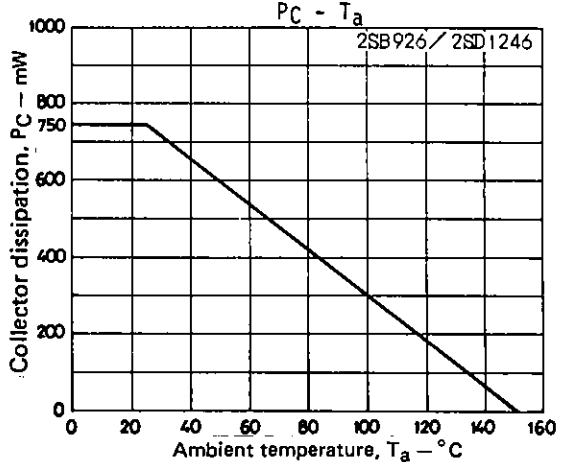
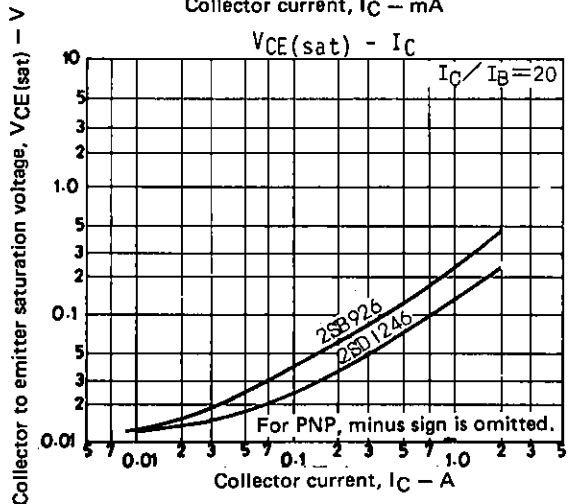
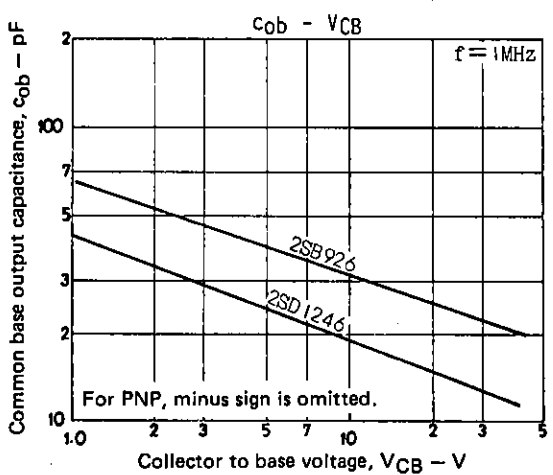
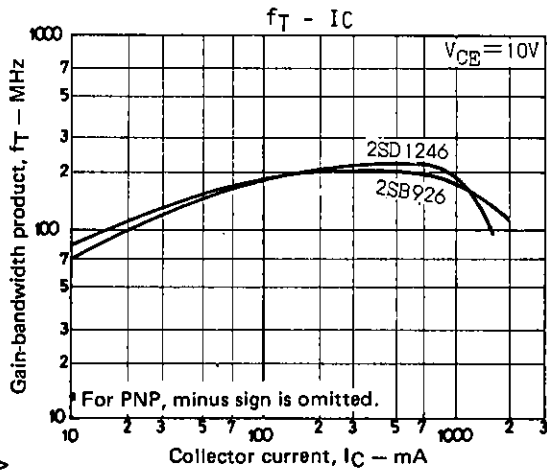
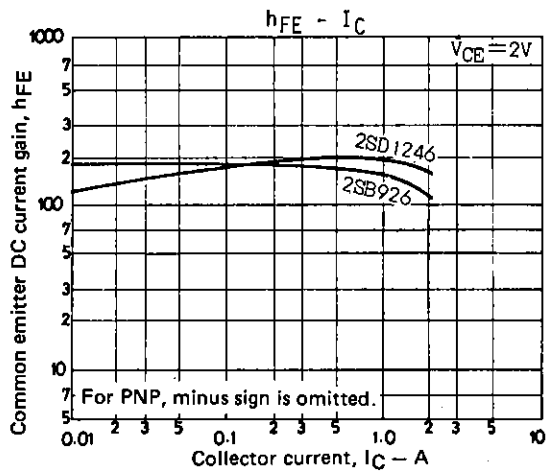
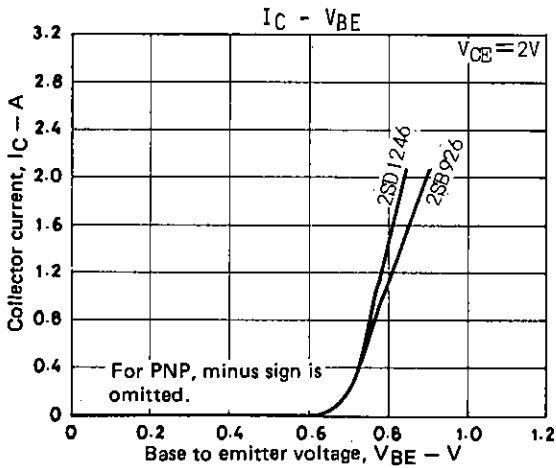
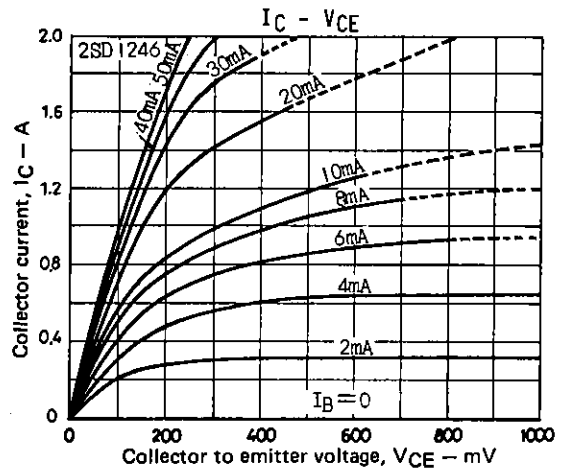
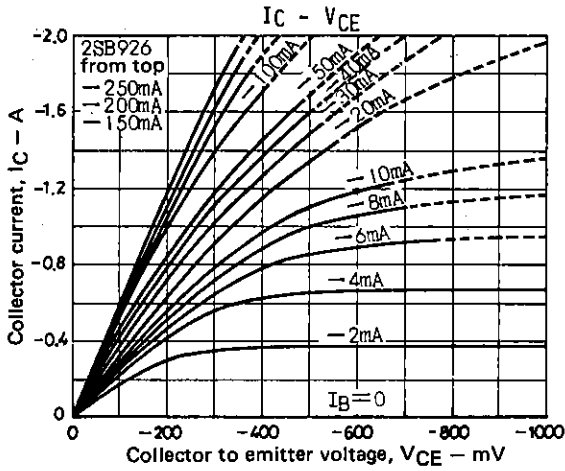
Electrical Characteristics/ $T_a = 25^\circ\text{C}$ 

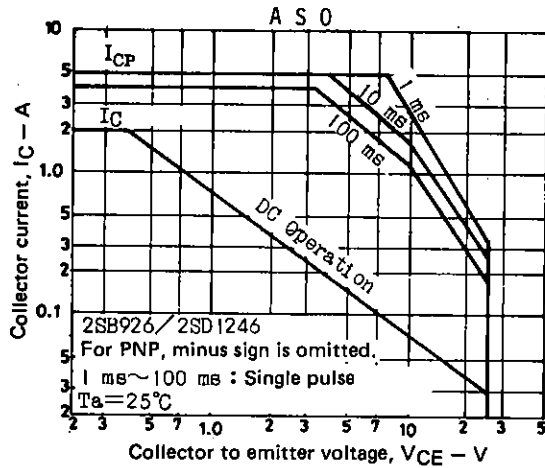
			min	typ	max	unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = (-)20\text{ V}, I_E = 0$			(-) $0.1$	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = (-)4\text{ V}, I_C = 0$			(-) $0.1$	$\mu\text{A}$
DC current gain	$h_{FE}(1)$	$V_{CE} = (-)2\text{ V}, I_C = (-)100\text{ mA}$	$100^*$		$560^*$	
	$h_{FE}(2)$	$V_{CE} = (-)2\text{ V}, I_C = (-)1.5\text{ A, pulse}$	$65$	$130$		
Gain-bandwidth product	$f_T$	$V_{CE} = (-)10\text{ V}, I_C = (-)50\text{ mA}$		$150$		MHz
Common base output capacitance	$c_{ob}$	$V_{CB} = (-)10\text{ V}, f = 1\text{ MHz}$		$19$		pF
				$(32)$		
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = (-)1.5\text{ A}, I_B = (-)75\text{ mA, pulse}$		$0.18$	$0.4$	V
				$(-0.35)$	$(-0.6)$	
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = (-)1.5\text{ A}, I_B = (-)75\text{ mA}$		$(-0.85)$	$(-1.2)$	V
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = (-)10\text{ }\mu\text{A}, I_E = 0$	$(-)30$			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{ mA}, R_{BE} = \infty$	$(-)25$			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = (-)10\text{ }\mu\text{A}, I_C = 0$	$(-)6$			V

\* The 2SB926/2SD1246 are classified by 100 mA  $h_{FE}$  as follows:

100 R	200	140 S	280	200 T	400	280 U	560
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**Package Dimensions 2003A**  
(unit: mm)





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